

**Silicon PNP Power Transistors****2SA1079****DESCRIPTION**

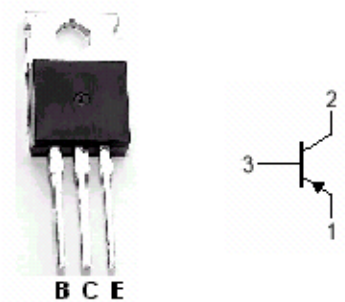
- With TO-220 package
- High transition frequency
- Excellent safe operating area

APPLICATIONS

- High-frequency power amplifier
- Audio power amplifiers and drivers

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector; connected to mounting base
3	Base

**Fig.1 simplified outline (TO-220) and symbol****Absolute maximum ratings (Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-160	V
V_{CEO}	Collector-emitter voltage	Open base	-160	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-2	A
P_C	Collector power dissipation	$T_C=25^{\circ}\text{C}$	25	W
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-65~150	$^{\circ}\text{C}$

**Silicon PNP Power Transistors****2SA1079****CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-1mA, R _{BE} =∞	-160			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-1 μ A, I _E =0	-160			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1 μ A, I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-0.7A; I _B =-70mA		-0.45	-1.0	V
V _{BE}	Base-emitter on voltage	I _C =-0.7A; V _{CE} =-5V		-0.8	-1.7	V
I _{CBO}	Collector cut-off current	V _{CB} =-160V; I _E =0			-1	μ A
I _{CEO}	Collector cut-off current	V _{CE} =-160V; I _B =0			-100	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-1	μ A
h _{FE-1}	DC current gain	I _C =-0.3A; V _{CE} =-5V	100		350	
h _{FE-2}	DC current gain	I _C =-0.7A; V _{CE} =-5V	50			
f _T	Transition frequency	I _C =-0.5A; V _{CE} =-10V; f=10MHz		120		MHz
C _{OB}	Output capacitance	I _E =0; V _{CB} =-20V; f=1MHz		100		pF



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PACKAGE OUTLINE

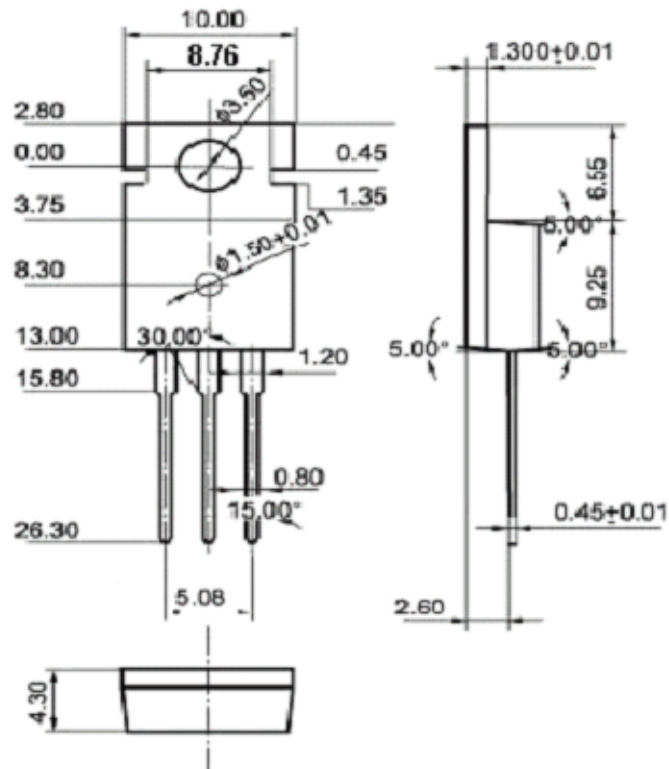


Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)